

IGBT

Features

- 1000V, 60A, $V_{CE(sat)(typ.)}=2.2V@V_{GE}=15V$
- Lower losses
- Higher system efficiency
- Excellent short-circuit capability
- Square RBSOA

General Description

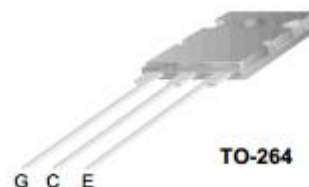
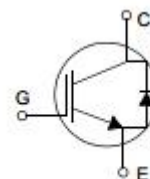
DAXIN's IGBTs offer lower losses and higher energy for application such as motor drive, inverter and other soft switching applications.

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	1000	V
V_{GES}	Gate-Emitter Voltage	± 30	V
I_C	Continuous Collector Current ($T_C=25^\circ C$)	120	A
	Continuous Collector Current ($T_C=100^\circ C$)	60	A
I_{CM}	Pulsed Collector Current (Note 1)	300	A
I_F	Diode Continuous Forward Current ($T_C=100^\circ C$)	75	A
I_{FM}	Diode Maximum Forward Current (Note 1)	300	A
t_{sc}	Short Circuit Withstand Time	10	us
I_{sc}	Short Circuit Current	360	A
P_D	Maximum Power Dissipation ($T_C=25^\circ C$)	833	W
	Maximum Power Dissipation ($T_C=100^\circ C$)	333	W
T_J	Operating Junction Temperature Range	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{th j-c}$	Thermal Resistance, Junction to case for IGBT	0.15	$^\circ C/W$
$R_{th j-c}$	Thermal Resistance, Junction to case for Diode	0.74	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	40	$^\circ C/W$



Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE}=0V, I_C=250\mu A$	1000	-	-	V
I_{CES}	Collector-Emitter Leakage Current	$V_{CE}=1000V, V_{GE}=0V$	-	-	250	μA
I_{GES}	Gate Leakage Current, Forward	$V_{GE}=30V, V_{CE}=0V$	-	-	100	nA
	Gate Leakage Current, Reverse	$V_{GE}=-30V, V_{CE}=0V$	-	-	-100	nA
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE}=V_{CE}, I_C=250\mu A$	4.5	-	5.7	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=60A$	-	2.2	2.5	V
Q_g	Total Gate Charge	$V_{CC}=960V$ $V_{GE}=15V$ $I_C=60A$	-	490		nC
Q_{ge}	Gate-Emitter Charge		-	36		nC
Q_{gc}	Gate-Collector Charge		-	300		nC
$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600V$ $V_{GE}=15V$ $I_C=60A$ $R_G=10\Omega$ Inductive Load $T_C=25^\circ\text{C}$	-	52	-	ns
t_r	Turn-on Rise Time		-	154	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	538	-	ns
t_f	Turn-off Fall Time		-	82	-	ns
E_{on}	Turn-on Switching Loss		-	10.0	-	mJ
E_{off}	Turn-off Switching Loss		-	6.2	-	mJ
E_{ts}	Total Switching Loss		-	16.20	-	mJ
C_{ies}	Input Capacitance	$V_{CE}=25V$ $V_{GE}=0V$ $f=1\text{MHz}$	-	3600	-	pF
C_{oes}	Output Capacitance		-	480	-	pF
C_{res}	Reverse Transfer Capacitance		-	313	-	pF
R_{Gint}	Integrated gate resistor	$f=1\text{M}; V_{pp}=1V$		3.75		Ω

Electrical Characteristics of Diode ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	$I_F=60A$	-	1.9	2.2	V
t_{rr}	Diode Reverse Recovery Time	$V_{CE}=600V, I_F=60A$ $dI_F/dt=500A/\mu s$	-	239		ns
I_{rr}	Diode peak Reverse Recovery Current		-	27	-	A
Q_{rr}	Diode Reverse Recovery Charge		-	2399	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature